

10-1500 MHz LOW NOISE TO-8 CASCADABLE **AMPLIFIER**

HAMP-1004 HAMP-1004TXV

TECHNICAL DATA

Features

WIDE 1 dB BANDWIDTH 5-1650 MHz

LOW NOISE FIGURE 4.0 dB at 1500 MHz

EXCEPTIONAL PHASE LINEARITY 1.7 Degree Deviation from 100 to 1500 MHz

LOW VARIATION OVER TEMPERATURE

EASILY CASCADABLE IN A 50 OHM SYSTEM

Description/Applications

The HAMP-1004 is a thin-film hybrid amplifier using bipolar transistors. The design uses resistive feedback which provides exceptional phase linearity and high performance over a wide temperature range and bandwidth. The internal bias network and coupling capacitors eliminate the need for external support circuitry.

This amplifier is ideal for IF, RF and high speed digital applications.

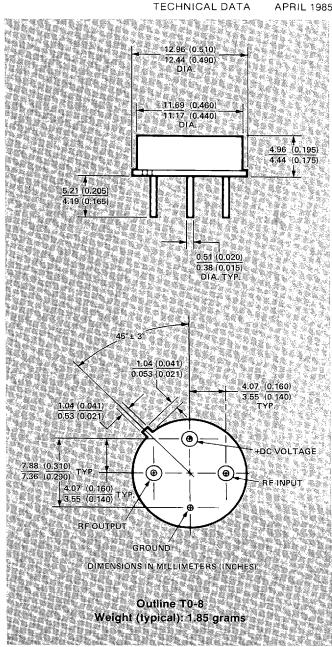
The HAMP-1004 is supplied in a standard rugged four leaded T0-8 hermetic package.

Absolute Maximum Ratings*

DC Voltage 30.0 V
Continuous RF Input Power +15 dBm
Short Term RF Input Power +20 dBm
(CW/1 Minute Duration)
Max. Input Peak Power +27 dBm
(3 Microsecond Pulse, One Single Pulse)
Operating Case Temperature55° C to 125° C
Storage Temperature65° C to 150° C

^{*}Operation in excess of any one of these conditions may result in permanent damage to this device.

MTTF: (Calculated, MIL-STD-217D): 1.2 x 107 Hours at Case Temperature +85° C.



Electrical Specifications (Measured in 50 Ohm System at +15 V)

Characteristic	Typical	Guaranteed			
	at 25° C	0-50°C	55+85° C.		
Frequency Range (MHz)	10-1500	10-1500+ 71-7-	- 10-1500 - 1		
1 dB Bandwidth (MHz)	5-1650				
Gain Max. (dB)	13.4	14.2	14.5		
Gain Min. (dB)	12.5	<u> </u>	11.0, / /		
Gain Flatness Max.(dB)	±0.3	110:717	+1.1.3		
Maximum Deviation from Linear Phase 100-1500 MHz (°)	1.7				
Noise Figure (Max.) (dB)	4.0	5.0 ° †			

Characteristic	Typical	Guaranteed		
	at 25°C	0-50°C	55+85°C	
Power Output at 1 dB Compression (Min.) (dBm)	1.0	++1.0 ±	-3.5 	
VSWR Input/Output Max			2.0	
Second Order Harmonic Intercept Point (dBm)	25.0	+ 11 1		
Second Order Two Tone Intercept Point (dBm)	20.0			
Third Order Two Tone Intercept Point (dBm)	12.0			
LIDC Current ImA)	18.0	+1+1T	11/4/472	

Typical Performance

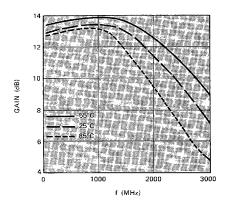


Figure 1. Gain at Three Temperatures

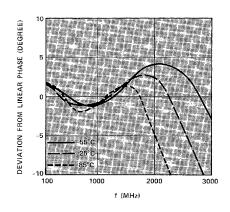


Figure 2. Phase at Three Temperatures

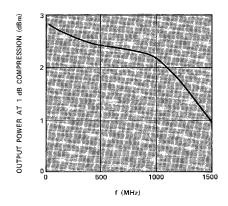


Figure 3. P_{1dB} at 25° C

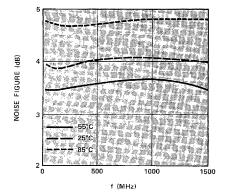


Figure 4. Noise Figure at Three Temperatures

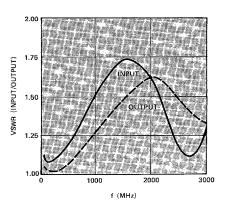


Figure 5. Input/Output VSWR at 25° C

Typical S-Parameters at 25°C

Frequency	Si Si	1	1 & 1 - 2 - 3 + 4 S 2 - 3 - 3 - 3 + 5 - 1		The second secon		S ₂₂	
(MHz)	⊤∦ Mag. ≒ .	Ang	Mag."	Ang.	Mag.	Ang.	Mag	Ang.
100	0.035	* / - 113	4.44		0.124	* 3 *	0.010	-132
200	0.027	84	4.47	163	0.126	1	## ±0.010 ##2	₹ 50
300	0.054	69	4.53	154	0.127]}## #6][∃	* * * 0.022 * * *	27
400	0.073	55	4.55	146	0.125		0.032	25
500	0.090	42	4.57	136	0.133	-14	0.036	20
600	0.117	28	4.60	127	0.133	*** -15 ***	0.049	5
700	**0.138	-14	4.63	118	0.129	-20	0.064	
800	0.159		4.65	108	0.129	-22	0.081	22
900	0.184	-10	4.68	98	0.133	* - - 2 6 * * -	0.096	-31
1000	0.208	20	4.66	88	0.133	-29	0.119	**************************************
1100	0.226	-30	4.65	78	0.132	** ** ±31	* * +0.137 * * -	± 4 3
1200	0.240	-40	4.65	69	0.136	34	0.146	3 T 3 T 5 T 1 T T T T T T T T T T T T T T T T
1300	0.251	-50	4.59	58	0.136	-37	0.162	59
1400	0.260	-59	4.51	48	0.138	## -41 ** *	- 0.175	-69
1500	0.270	71	4.40	38	0.136	-43	0.197	
1600	0.274	-81	4.30	- 28	0.134	-46	0.205	* * *
1700	0.271	-91	4.09	17	0.138	49	0.222	95
1800	0.259	=102	3.93	8	0.140	51	0.224	-104 l
1900	0.247	-112	3.81		0.139	-54	0.233	-110 ·
2000	. 0.230	123	3.63		0.140	** -57 * * ·	0.237	\$ \$ \$ -117 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
2100	0.219	-130	3.51	20	0.147	-60	0.235	-124
2200	0.191	-136	3,33	-28	0.148	63	0.228	*.*131
2300	0.163	-143	3.16	-37	0.150	66	0.220	-138
2400	0.126	152	3.00	4-45	0.154	69	0.207	147
2500	0.093	- 165	2.88	-54	0.158	+-72	0.198	156
2600	0.065	172	2.73	-62	0.161	- - 7 6 •	0.189	-162
2700	0.048	127	2.62	-69	0.166	-79	0.176	169
2800	0.064	83 🖷	2.50	-77	0.169	83 -	0.160	176
2900	0.092	60	2.39	85	0.171	* 85 * *	0.142	176
3000	###0,118###	42	2.28	∓9 2	0.178	89.	0.139	163

Typical Performance Parameters at 25°C

Frequency (MHz)	Linear Phase Deviation (deg.)	Relative Phase (deg.)	Gain Deviation (dB)	Gain Absolute (dB)	Group Delay (ns)	Input	Output VSWR
10	SPRANTE TO THE	W. 2 * W. L.	T. Particial Comments	** 12.90 * * *		1.30	1:20
100	1.59	0.1	0.25	12.95	0.31	1.07	1.02
200	*	15 - 9	-0,20	13.00	0.26	1.06	1.02
300	* * * 0.70 · · · ·	18 18	-0.08	* 13.12 * · ·	0.25	Lavarr. C. sak	1.04
400	-0.28	-27	0.04	13.16	0.24	1.16	1.07
500	-0.66	36	0.01	13.19	0.26	1.20	1.08
600	-0.84	46	0.05	13.25	0.26	1.26	1.10
700	-1.07	55	0.12	13.32	0.26	1.32	1,14
800	1.34 -	65	0.15	13.35	0.26	1.38	1.18
900	-0.98	75	0.20	13.40	0.28	1.45	1.21
1000	-0.93	-84	0.17	13.37	0.27	1.53	1.27
1100	## = 0.45	- 94	0.15	13.35	0.28	1.58	1.32
1200	-0.44	-104	0.15	13.35	0.27	1.63	1.34
1300	0.56	115	0.04	13.24	0.30	1.67	1.89
1400	.1.27	⊢125 · · ·	-0.11	13.09	0.29	1.70	1,42
1500	1.66	-135	-0.33	12.87	0.28	1.74	149
1600	2.09	-145	0.53	12.67	0.28	1.76	1.52
1700	3.17	-156	-0.97	12.23	0.30	174	**** 1.57 ************************************
1800	2.39	165 · ·	-1.31	11.89	0.25	1.70	1.58
1900	2.00	-174	1.57	11,63	0.26	1.66	# 16. E 18.
2000	1,91	_183 ⊪	-2.01	11,19	0.27	1.60	1.62
2100	1.21	-192	-2.29	10.91	0.25	1.56	1.62
	0.31	-201	-2.76	10.44	0.24	1.47	1.59
2300	0.48	-210	-3.20	10.00	0.25	1,39	L. 156
2400	-2/27	-218	-3.65	9.55	0.22	1.29	1.52
2500	-3:15	-227	-4.00	9.20	0.24	1.21	1.50
2600	4.70	-235	-4.48	8.72	0.22	1.14	1.47
2700	-7.49	241	4.82	8.38	0.19	1.10	1.43
2800	8.85	-250	-5,25	7.95	0.23	174, 114,	1.38
2900	-10.97	257	-5.62	7.58	0.21	1.20	1.33
3000	13.17	-265	-6.03	7.17	0.21	1.27	1.32

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AMPLIFIER PRODUCTS HIGH RELIABILITY

HAMP-1004TXV

Since the advantages of products tested to well established reliability screening standards can be of significant value to reliability oriented customers, HP makes available products with Hi-Rel screening and testing patterned after MIL-STD-883, Method 5004.2 latest revision.

The table below depicts the screening program for this family of amplifiers.

100% SCREENING PROGRAM

Screening Test/Inspection	MIL-STD-883 Test Method	Conditions/Comments
1. Internal Visual Inspection (PreCap)	2017	经分别的 化二十二十二十二十二十二十二十二十二十二十二十二十二十二十二十二十二十二十二十
High Temperature Storage Stabilization Baker	1008	Condition B $T = 125^{\circ}C$, $t = 24$ hours
3. Temperature Cycling	1010	Condition B -55° to 125° C
4. Constant Acceleration	2001	Condition B 20 kg/s, Y ₁ Direction
5. Pre Burn-in Electrical		Per Applicable Device Specification
6 Burn-in	1015	t = 168 hours Tc = 80% of Rated Case Temp. and 80% of Rated Bias Conditions
7. Post Burn-in Electrical (PDA ≤ 10%)		Per Applicable Device Specification
8. Hermeticity Tests (Fine and Gross)]/-/-1014/]/-/-/	Conditions A and C
9 Final Electrical Tests		Per Applicable Device Specification
10. External Visual Inspection	2009	をして、または、ないないない。

Note: Additional tests, screens and qualification testings (e.g.: X-ray, PIND, Extended Burn-in, Group A, B, C and D) are available on request.

Ordering Information

Add suffix TXV to standard part number.

Example: Standard Product

Hi-Rel Product

HAMP-1004 HAMP-1004TXV

4447584 OO16796 11C **==**

For more information call your local HP sales office listed in the telephone directory white pages. Ask for the Components Department. Or write to Hewlett-Packard: U.S.A. — P.O. Box 10301, Palo Alto, CA 94303-0890. Europe — P.O. Box 999 1180 AZ Amstelveen. The Netherlands, Canada — 6877 Goreway Drive, Mississauga, L4V 1M8, Ontario. Japan — Yokogawa-Hewlett-Packard Ltd., 3-29-21, Takaido-Higashi, Suginami-ku, Tokyo 168, Elsewhere in the world, write to Hewlett-Packard Intercontinental, 3495 Deer Creek Road, Palo Alto, CA 94304.

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